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INFORMATION DISCLOSURE				Filing Date	Concurrently Horowith 319 2004			
STATEMENT BY APPLICANT (use as many sheets as necessary)				First Named Inventor	Young-pil Kim et al.			
			•	Group Art Unit	Unknown 2015			
			•	Examiner Name	Hinknown Landau			
Sheet	1	of	1	Attorney Docket Number	5649-1276			

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L		OTHER NON PATENT LITERATURE DOCUMENTS	
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Examiner Signature	Marche C. 1	anker	Date Considered	7	/16/	26

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include capy of this form with next communication to applicant.